

# BUK652R7-30C

N-channel TrenchMOS intermediate level FET

Rev. 02 — 16 December 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a>	<a href="#">11</a>	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	204	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	2.72	3.3	mΩ
		$V_{GS} = 5\text{ V}; I_D = 15\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 15</a>	-	11.1	13	mΩ



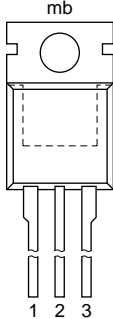
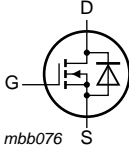
**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped	-	-	501	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 24\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 17</a> ; see <a href="#">Figure 18</a>	-	33.3	-	nC

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78A (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK652R7-30C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	30	V	
$V_{GS}$	gate-source voltage	DC	[1]	-16	16	V
		Pulsed	[2]	-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	[3]	-	100	A
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	[3]	-	100	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; see <a href="#">Figure 3</a>	-	721	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	204	W	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	[3]	-	100	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	721	A	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped	-	501	mJ	
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs

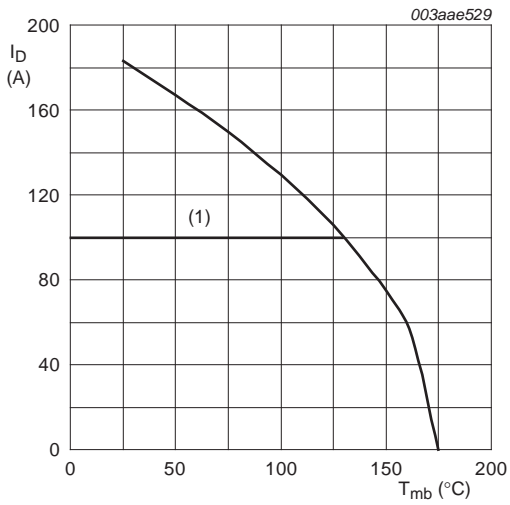
[2] Accumulated pulse duration not to exceed 5mins.

[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

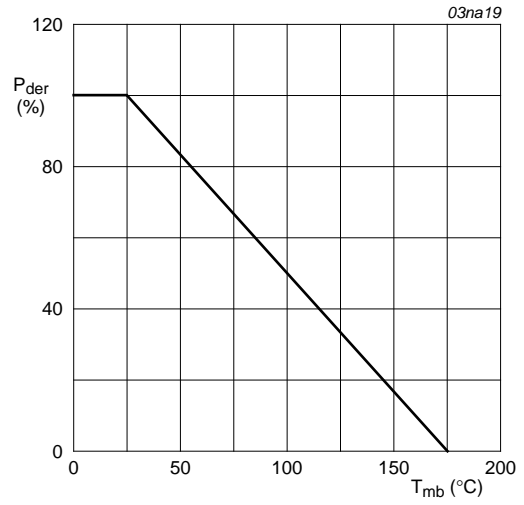
[6] Refer to application note AN10273 for further information.



$V_{GS} \geq 10\text{ V}$

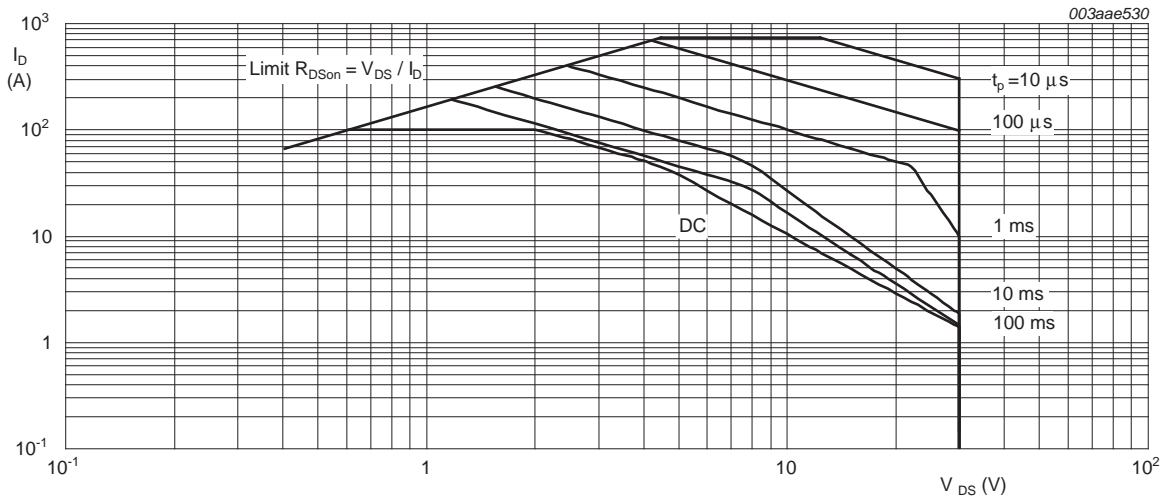
(1) capped at 100 A due to package

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



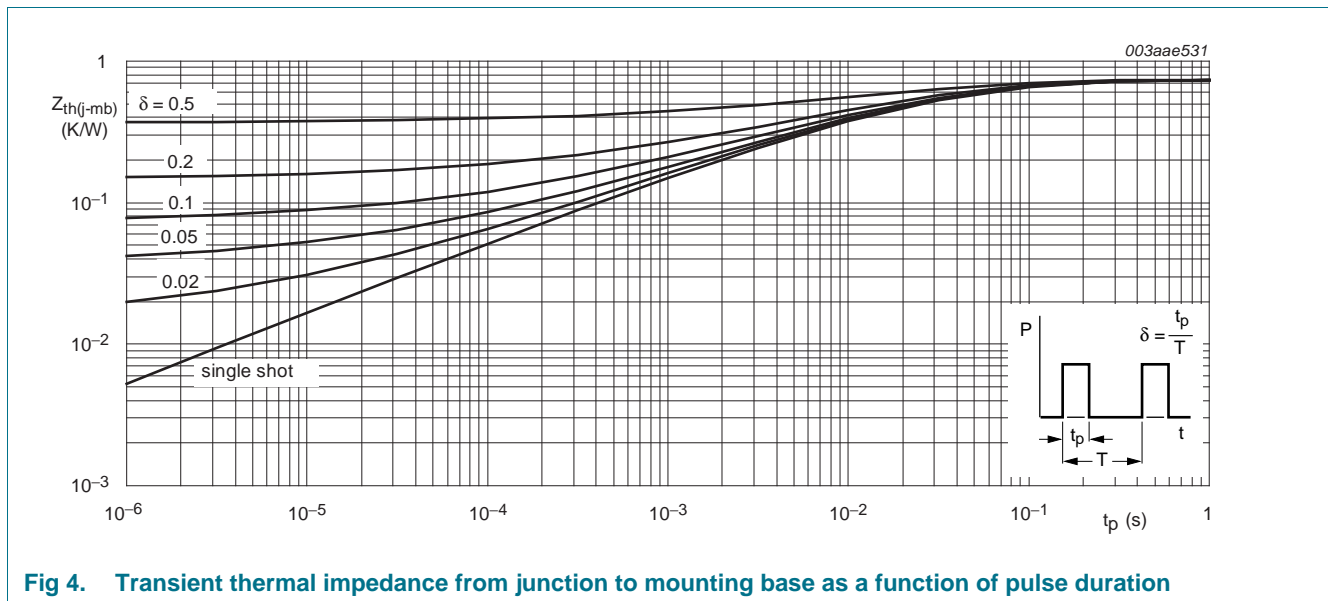
$T_{mb} = 25^\circ\text{C}$ ;  $I_{DM}$  is a single pulse

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

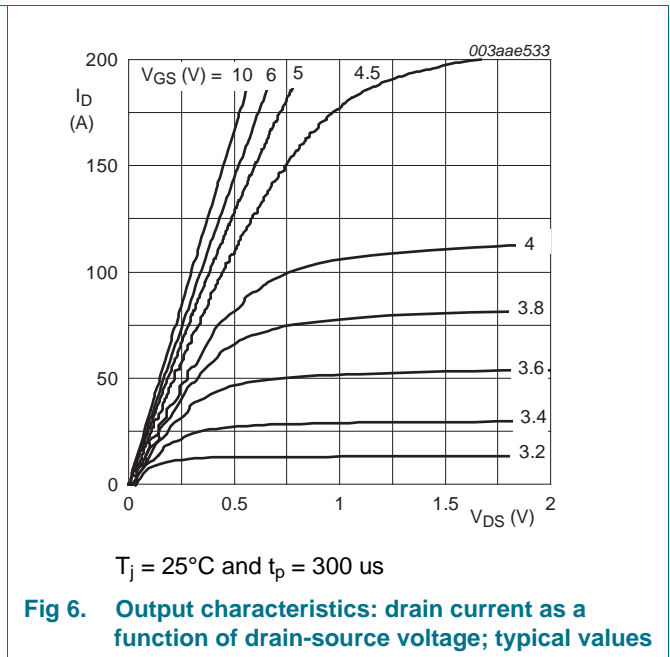
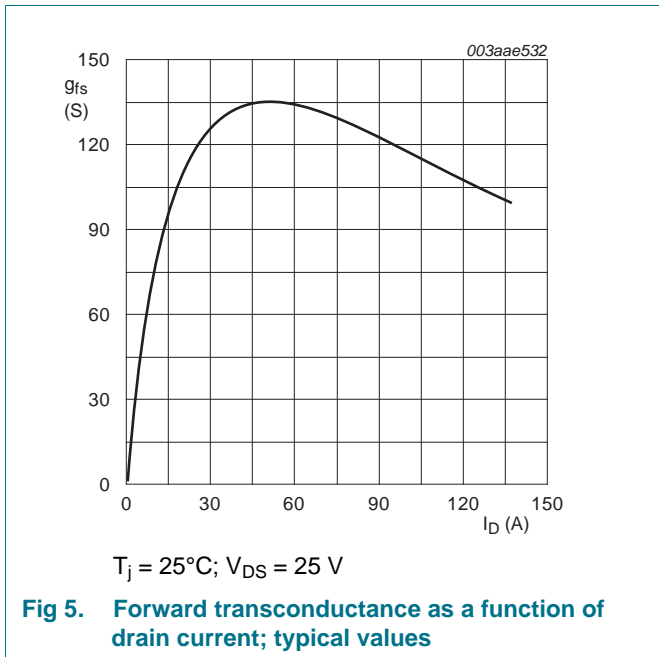
## 6. Characteristics

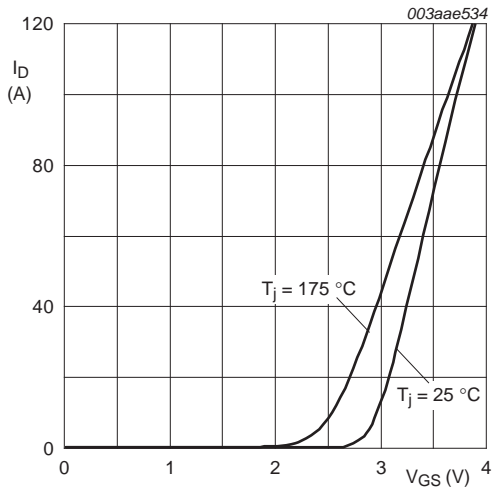
**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
			27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	1.1	1.5	2	V
		$I_D = 2.5 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	0.8	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	2.72	3.3	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	11.1	13	m $\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	3.9	5.3	m $\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	11.4	12	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	10	11.7	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	3.45	4.4	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	5.75	6.3	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a> ; see <a href="#">Figure 17</a>	-	5.9	-	C
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 17</a> ; see <a href="#">Figure 18</a>	-	114	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ see <a href="#">Figure 17</a> ; see <a href="#">Figure 18</a>	-	66	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ see <a href="#">Figure 17</a> ; see <a href="#">Figure 18</a>	-	18	-	nC
$Q_{GD}$	gate-drain charge		-	33.3	-	nC

**Table 6. Characteristics ...continued**

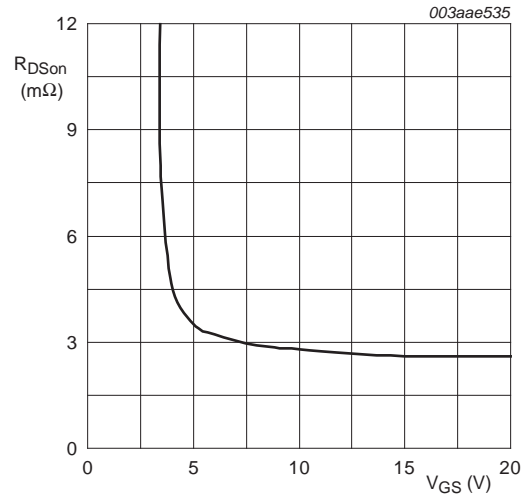
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 19</a>	-	5216	6960	pF
$C_{oss}$	output capacitance		-	896	1100	pF
$C_{rss}$	reverse transfer capacitance		-	537	740	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 25\text{ V}; R_L = 1\ \Omega; V_{GS} = 10\text{ V};$ $R_{G(ext)} = 10\ \Omega$	-	22	-	ns
$t_r$	rise time		-	59	-	ns
$t_{d(off)}$	turn-off delay time		-	209	-	ns
$t_f$	fall time		-	113	-	ns
$L_D$	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25\text{ }^\circ\text{C}$	-	4.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad ; $T_j = 25\text{ }^\circ\text{C}$	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 20</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}; dI_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 25\text{ V}$	-	50	-	ns
$Q_r$	recovered charge		-	73	-	nC





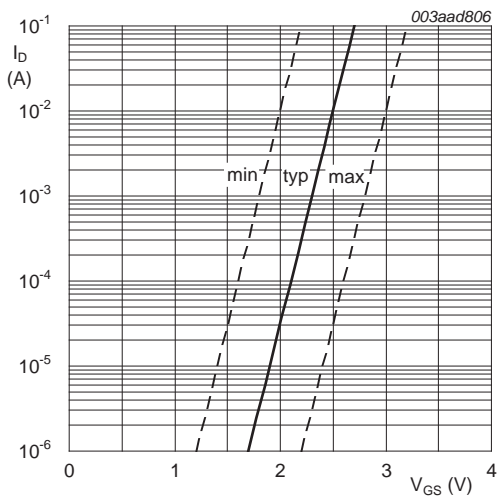
$V_{DS} = 25\text{ V}$

**Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



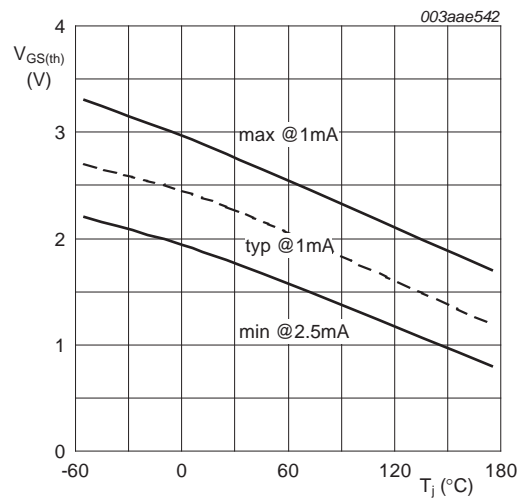
$T_j = 25\text{ }^\circ\text{C}; I_D 25\text{ A}$

**Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

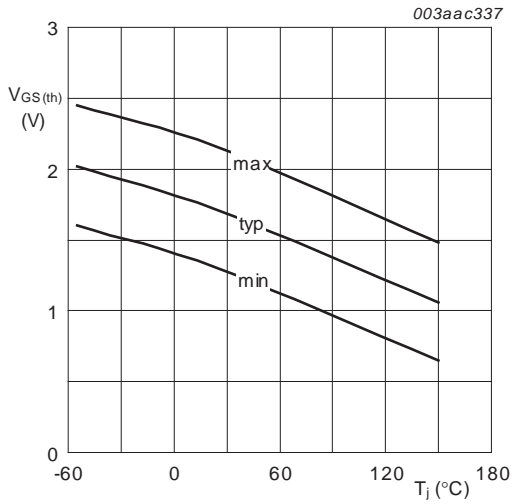
**Fig 9. Sub-threshold drain current as a function of gate-source voltage**



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

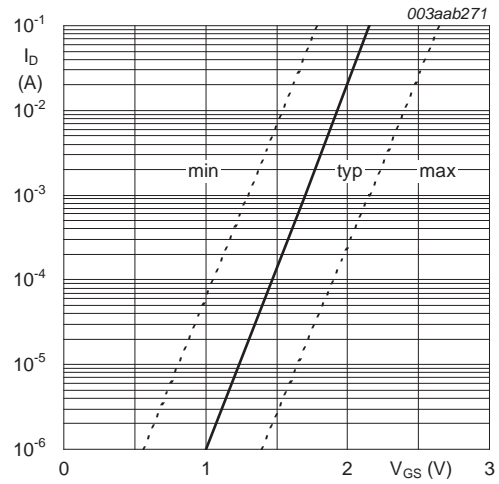
**Fig 10. Gate-source threshold voltage as a function of junction temperature**





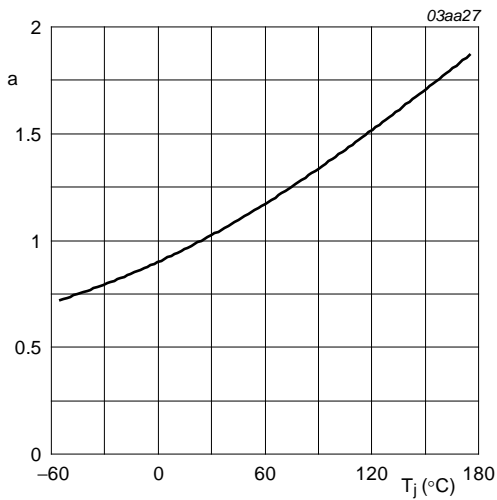
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

**Fig 11. Gate-source threshold voltage as a function of junction temperature**



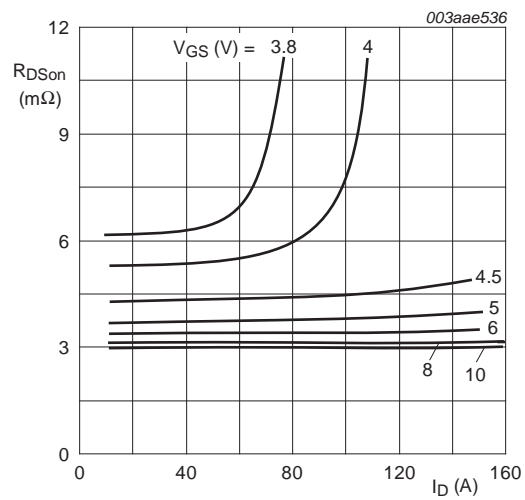
$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

**Fig 12. Sub-threshold drain current as a function of gate-source voltage**



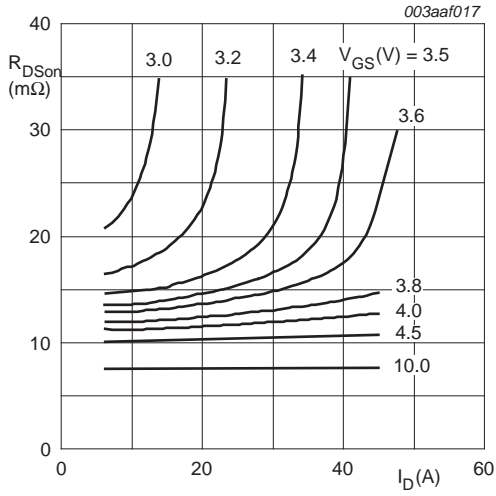
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

**Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature**



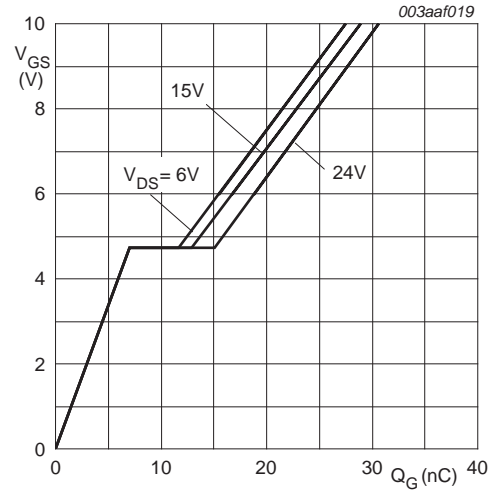
$$T_j = 25^\circ\text{C}; t_p = 300\ \mu\text{s}$$

**Fig 14. Drain-source on-state resistance as a function of drain current; typical values**



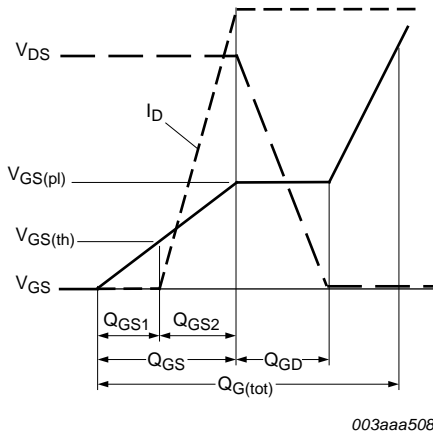
$T_j = 25^\circ\text{C}$

**Fig 15. Drain-source on-state resistance as a function of drain current; typical values**

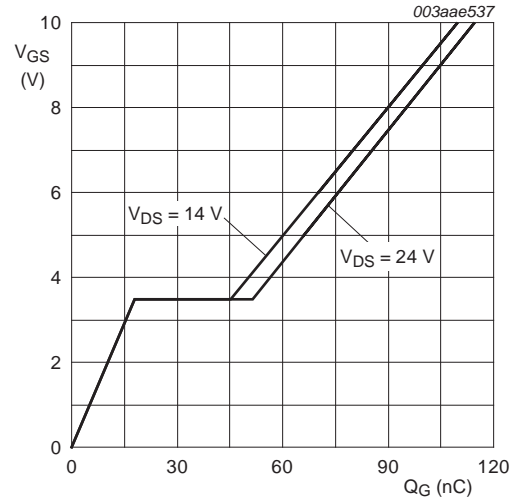


$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

**Fig 16. Gate-source voltage as a function of gate charge; typical values**

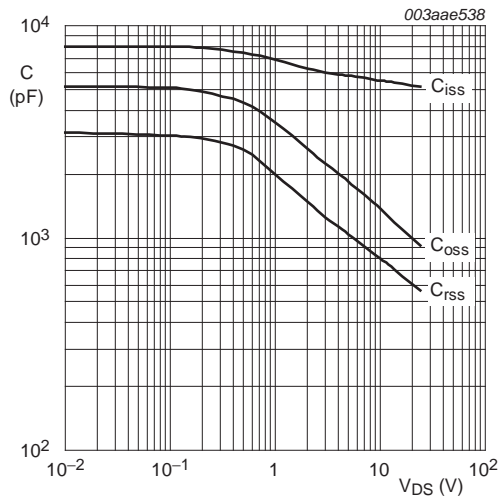


**Fig 17. Gate charge waveform definitions**



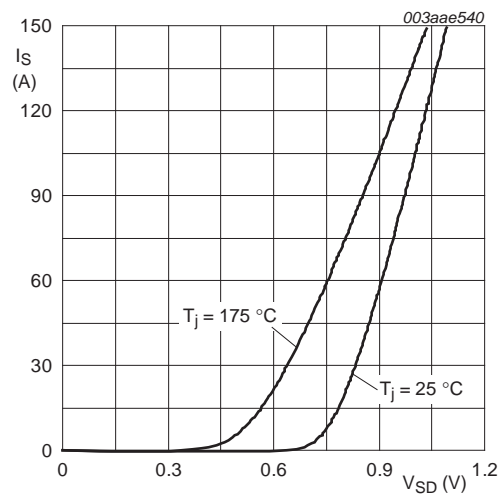
$T_j = 25^\circ\text{C}$  and  $I_D = 25\text{A}$

**Fig 18. Gate-source voltage as a function of gate charge; typical values**



V<sub>GS</sub> = 0 V; f = 1 MHz

**Fig 19. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



V<sub>GS</sub> = 0 V

**Fig 20. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A

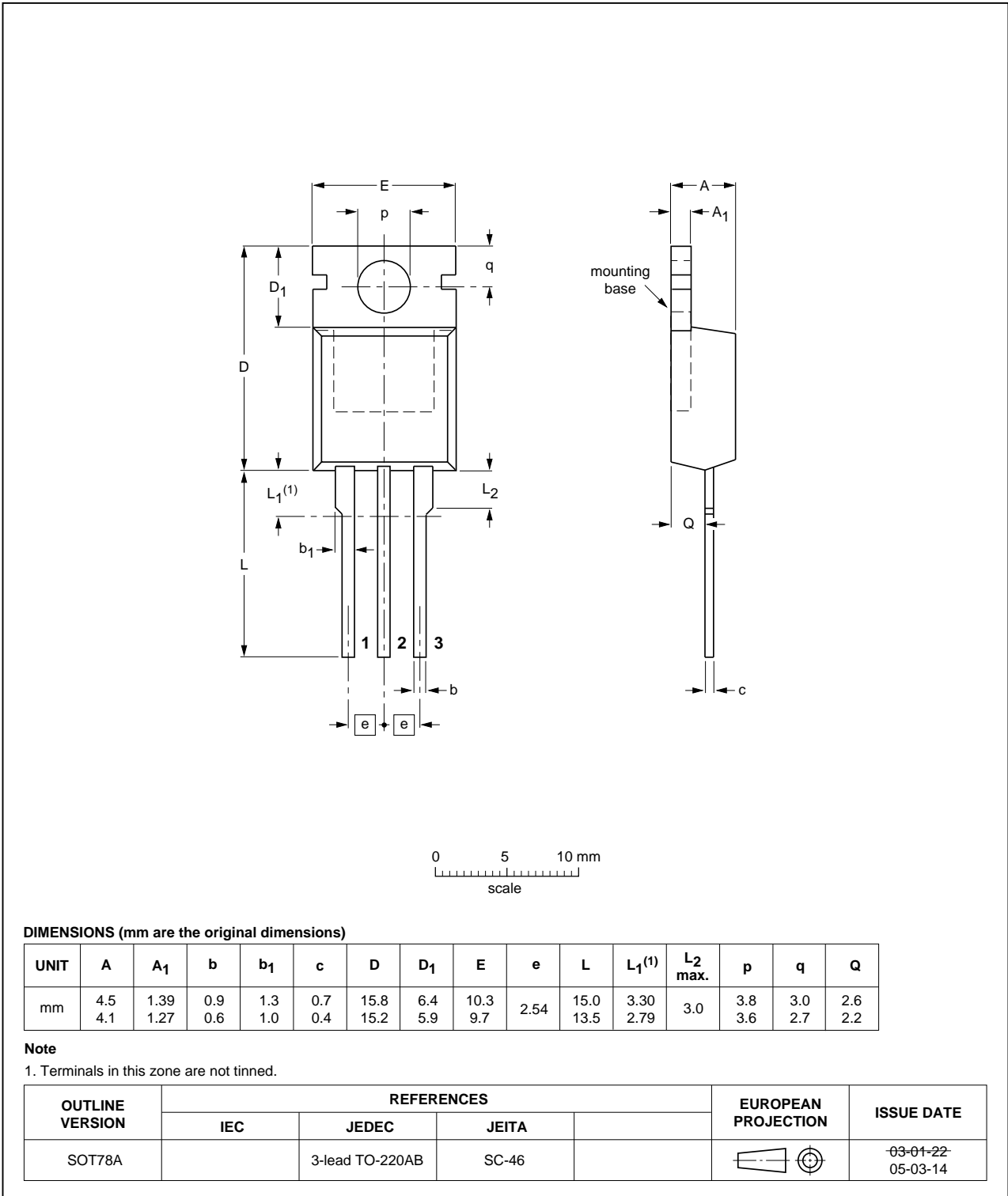


Fig 21. Package outline SOT78A (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK652R7-30C v.2	20101216	Product data sheet	-	BUK652R7-30C v.1
Modifications:	<ul style="list-style-type: none"><li>• Various changes to content.</li><li>• Status changed from Objective to Product.</li></ul>			
BUK652R7-30C v.1	20100705	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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